



55NM65-U3

Preliminary

Power MOSFET

**55A, 650V N-CHANNEL
SUPER-JUNCTION MOSFET**

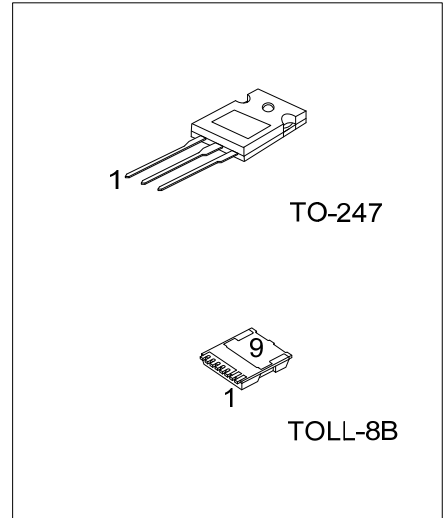
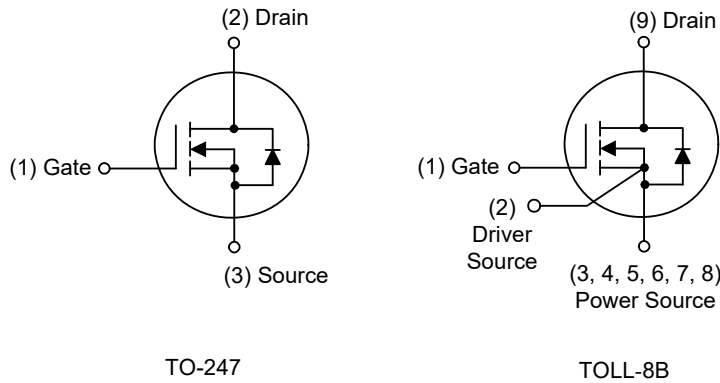
■ DESCRIPTION

The **UTC 55NM65-U3** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

■ FEATURES

- * $R_{DS(ON)} \leq 64 \text{ m}\Omega @ V_{GS}=10\text{V}, I_D=27.5\text{A}$
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness

■ SYMBOL



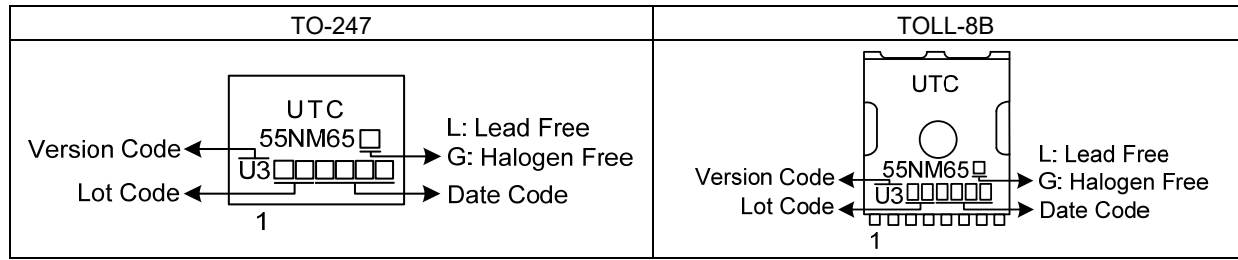
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment							Packing		
Lead Free	Halogen Free		1	2	3	4	5	6	7		8	9
55NM65L-U3-T47-T	55NM65G-U3-T47-T	TO-247	G	D	S	-	-	-	-	-	-	Tube
55NM65L-U3-T8B-R	55NM65G-U3-T8B-R	TOLL-8B	G	S	S	S	S	S	S	S	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>55NM65G-U3-T47-T</p> <p>(1) Packing Type (2) Package Type (3) Version Code (4) Green Package</p>	<p>(1) T: Tube, R: Tape Reel (2) T47: TO-247, T8B: TOLL-8B (3) Version U3 (4) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	55	A
	Pulsed (Note 2)	I_{DM}	165	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	1225	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	8.1	V/ns
Power Dissipation	TO-247	P_D	220	W
	TOLL-8B		312	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 100\text{mH}$, $I_{AS} = 4.9\text{A}$, $V_{DD} = 90\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 30\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-247	θ_{JA}	40	$^\circ\text{C}/\text{W}$
	TOLL-8B		35 (Note)	$^\circ\text{C}/\text{W}$
Junction to Case	TO-247	θ_{JC}	0.56	$^\circ\text{C}/\text{W}$
	TOLL-8B		0.4 (Note)	$^\circ\text{C}/\text{W}$

Note: Device mounted on FR-4 substrate P_c board, 2oz copper, with 1inch square copper plate.

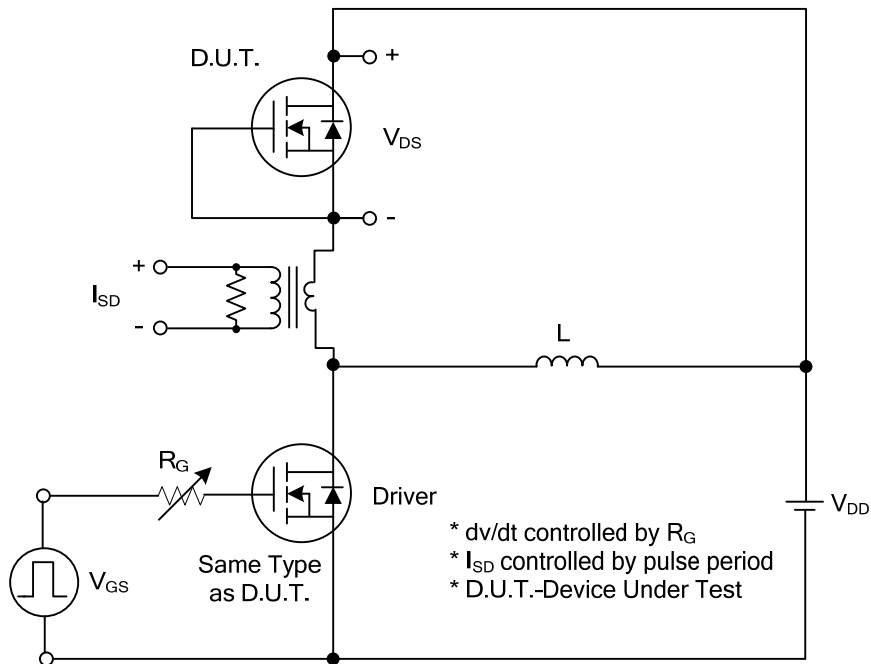
■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	650			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =650V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.5		4.5	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =27.5A			64	mΩ
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =50V, f=1MHz		3517		pF
Output Capacitance	C _{OSS}			1385		pF
Reverse Transfer Capacitance	C _{RSS}			81		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q _G	V _{DS} =520V, V _{GS} =10V, I _D =55A (Note 1, 2)		157		nC
Gate-Source Charge	Q _{GS}			28		nC
Gate-Drain Charge	Q _{DD}			98		nC
Turn-On Delay Time	t _{D(ON)}	V _{DD} =100V, V _{GS} =10V, I _D =55A, R _G =25Ω (Note 1, 2)		62		ns
Turn-On Rise Time	t _R			72		ns
Turn-Off Delay Time	t _{D(OFF)}			356		ns
Turn-Off Fall Time	t _F			117		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I _S				55	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				165	A
Drain-Source Diode Forward Voltage	V _{SD}	I _S =55A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time	t _{rr}	I _S =30A, V _{GS} =0V, dI _F /dt=100A/μs		672		ns
Body Diode Reverse Recovery Charge	Q _{rr}				15	

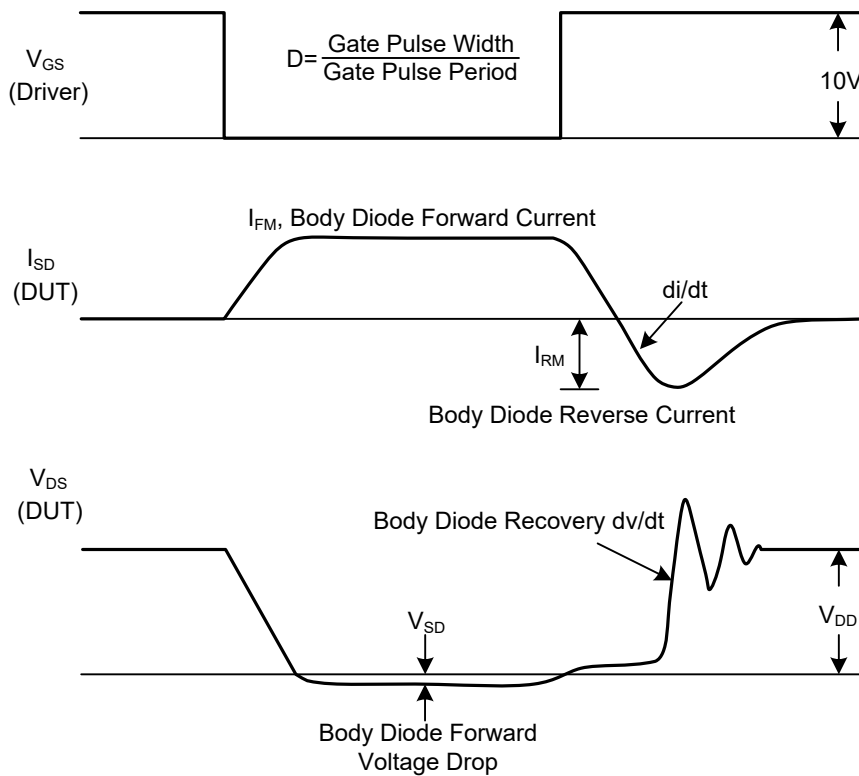
Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

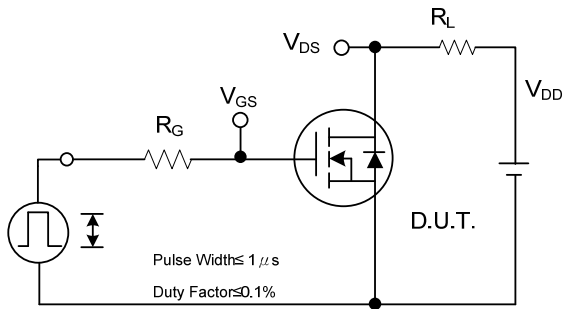


Peak Diode Recovery dv/dt Test Circuit

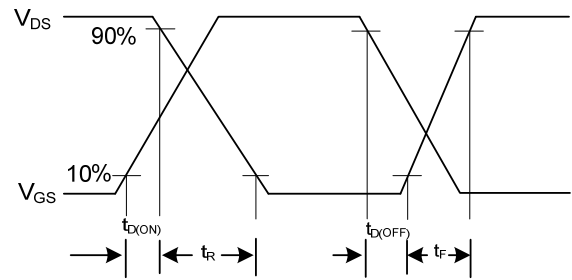


Peak Diode Recovery dv/dt Waveforms

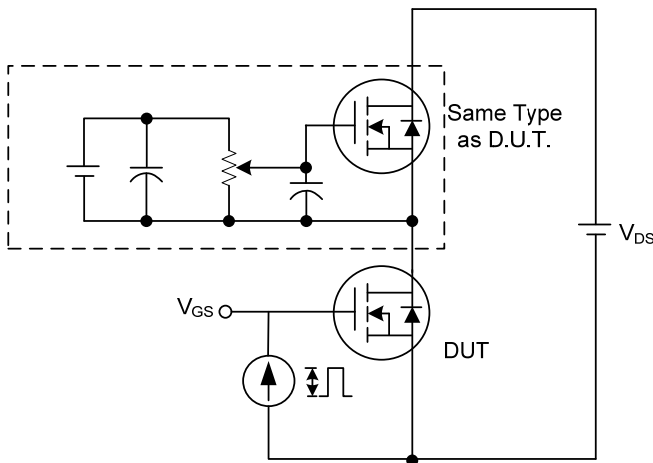
■ TEST CIRCUITS AND WAVEFORMS



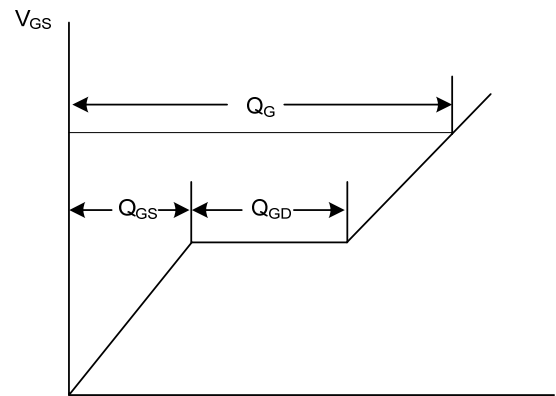
Switching Test Circuit



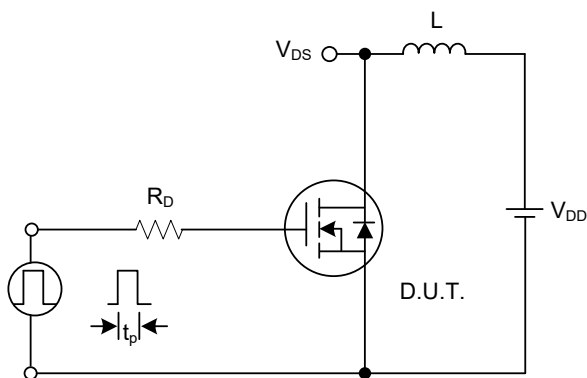
Switching Waveforms



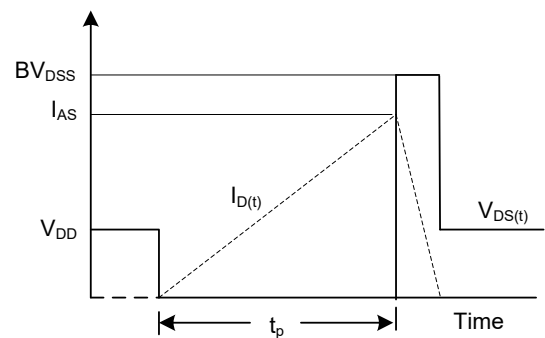
Gate Charge Test Circuit



Charge
Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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